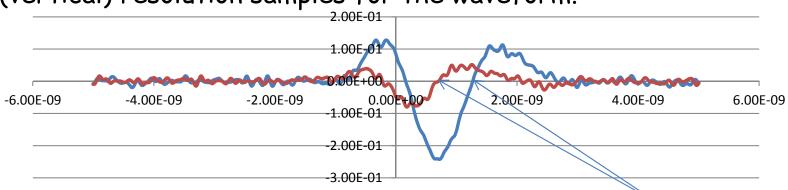
Noise reduction technique in APD time resolution measurement

C. Lu Princeton University (5/15/2012)



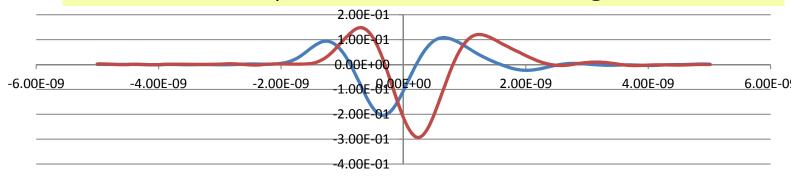
Digital scope in high resolution mode

Agilent digital scope has a "High Resolution Mode", which performs box-car averaging, averaging adjacent samples within a single capture of a waveform. This averaging provides lower noise and higher (vertical) resolution samples for the waveform.



Normal resolution mode, full BW @ 4GHz, sampling rate 20 GSa/sec.

I use these two points as the zero crossing references.



High
resolution
6.00E-09 mode, BW
reduced to
1.1 GHz,
sampling rate
reduced to
5 GSa/sec.



Time resolution with high resolution mode

Waveform data files are available here:

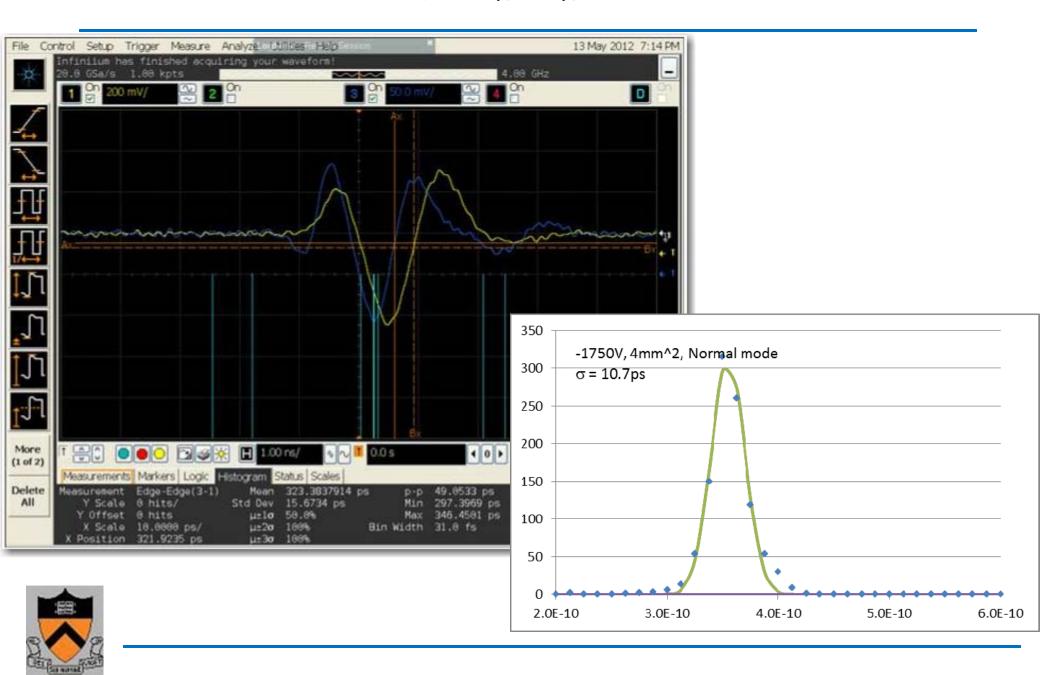
http://physics.princeton.edu/babar/fasttiming/05122012/4mm/1750V/

There are three subdirectories: ../No smooth; ../9bits and ../10bits, they are for three resolution modes. The data analysis results are as follows:

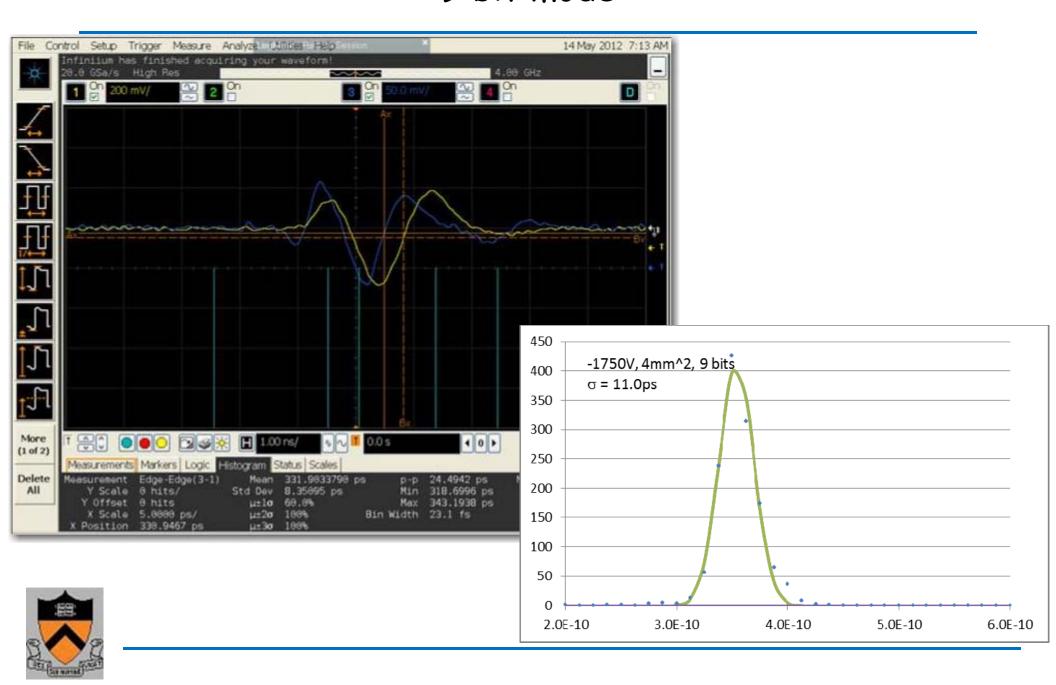
Scope Mode	Band width	Sampling rate	Single APD time resolution (ps)
Normal	4GHz	20Gsa/sec	10.7
9 bit	4GHz	20GSa/sec	9.9
10 bit	1.12GHz	5GSa/sec	8.3



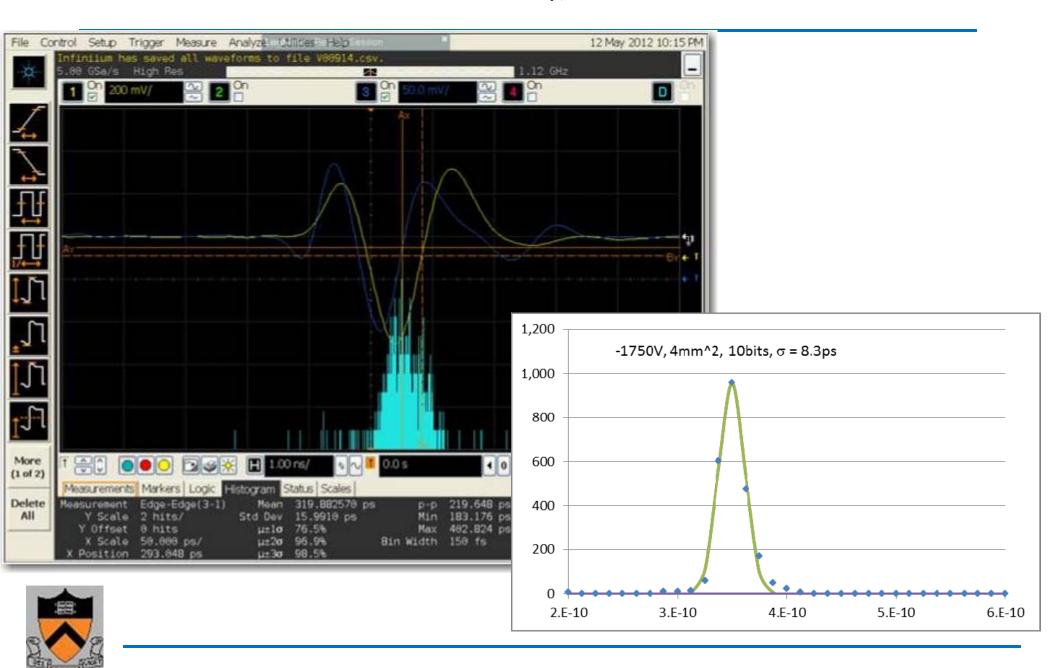
Normal mode



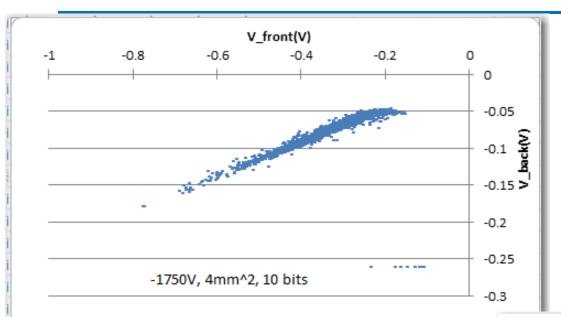
9 bit mode



10 bit mode



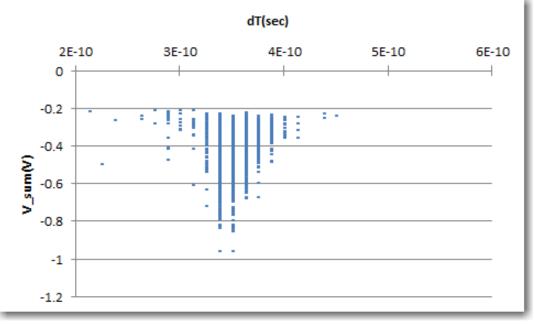
10 bit mode



Scatter plot of two APD's signal amplitudes

Scatter plot of dT vs. sum of two APDs signals.





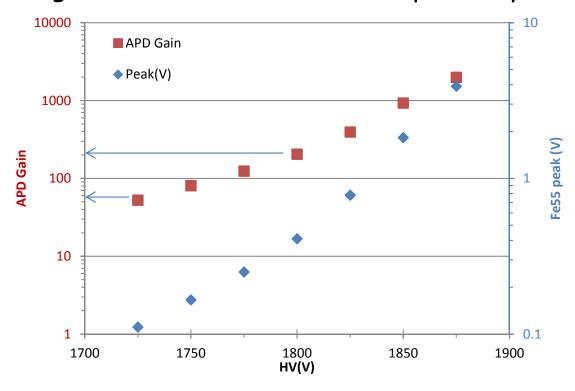
Summary

H.V. (V)	Resolution mode	Time resolution (ps)
-1800V	Normal	15.3
	9 bit	13.7
	10 bit	12.9
-1775V	Normal	12.9
	9 bit	10.8
	10 bit	9.7
-1750V	Normal	10.7
	9 bit	9.9
	10 bit	8.3
-1725V	Normal	10.96
	9 bit	9.4
	10 bit	7.1



Discussion

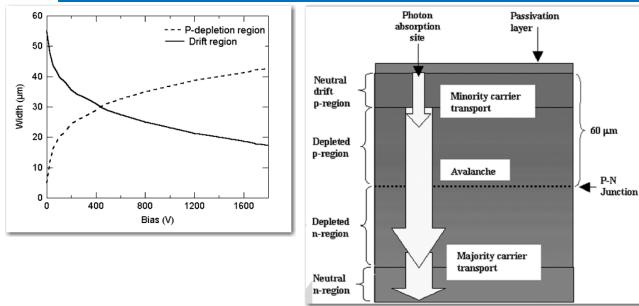
We have calibrated the APD gain with Fe-55 source. At 1725 V and 1800 V the APD gains are ~ 50 and ~ 200, respectively.

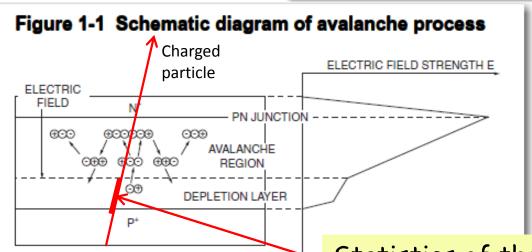


We saw the trend of lower HV corresponding to better time resolution. As the trigger condition are fixed for all these tests, at lower high voltage the events passing the trigger need to have larger primary e/hole pairs, that might reduce the primary statistical error.



Discussion (cont'd)





Typical electron mobility in silicon at room temperature is 1400 cm² /(V*s).

At ~ 1800 V, the P-depletion region is ~ 30 μ m. The APD avalanche

multiplication starts at electric field strength $\sim 2 \times 10^5$ V/cm, if we assume the E-field in the depletion region is 1/3 of this number, it would be $\sim 7 \times 10^4$ V/cm

The total drift time range across the P-depletion region would be 30×10^{-4} cm/ $(1400\times7\times10^{4}$ cm/s) = ~ 30 ps. This will contribute to the intrinsic time resolution of the APD.

Statistics of the primary ionization in this layer will dominate the time resolution.